Product data sheet

## 1. General description

PNP general-purpose double transistor in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package. NPN complement: BC847BS-Q.

### 2. Features and benefits

- · Low collector capacitance
- Low collector-emitter saturation voltage
- · Closely matched current gain
- Reduces number of components and boardspace
- No mutual interference between the transistors
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

· General purpose switching and amplification.

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-45	V
I <sub>C</sub>	collector current		-	-	-100	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	200	-	450	



### PNP general purpose double transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	D. D. D.	C1 B2 E2
2	B1	base TR1	6 5 4	
3	C2	collector TR2		(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	∐1 ∐2 ∐3	
6	C1	collector TR1	TSSOP6 (SOT363)	sym138

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BC857BS-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
BC857BS-Q	3F%

[1] % = placeholder for manufacturing site code

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### PNP general purpose double transistor

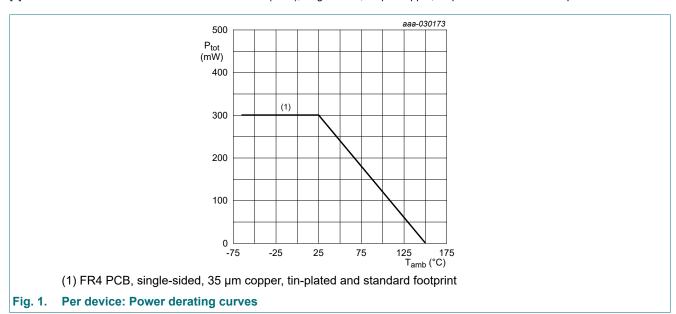
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor						
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-45	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-100	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-200	mA
I <sub>BM</sub>	peak base current			-	-200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	200	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Per device	•					•
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.



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#### PNP general purpose double transistor

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						-
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	568	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	230	K/W
Per device			1				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35  $\mu m$  copper, tin-plated and standard footprint.

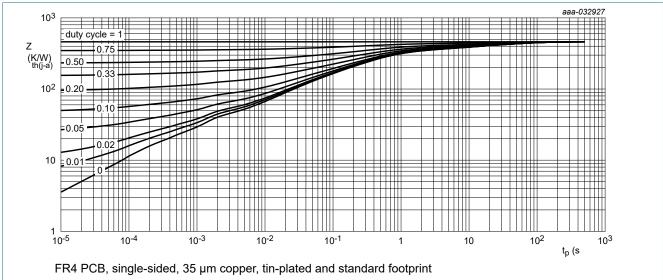


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

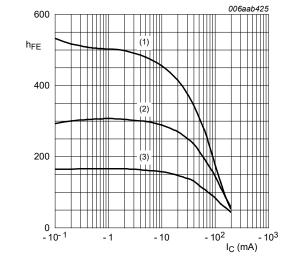
## PNP general purpose double transistor

# 10. Characteristics

## **Table 7. Characteristics**

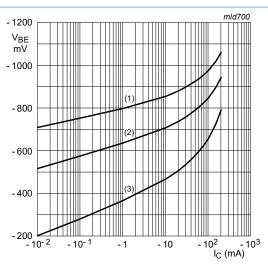
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	tor					
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	I <sub>C</sub> = -100 μA; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = -2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	45	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_C = 0 \text{ A}; I_E = -100 \mu\text{A}; T_{amb} = 25 \text{ °C}$	5	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-15	nA
	current	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-5	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -2 mA; T <sub>amb</sub> = 25 °C	200	-	450	
V <sub>CEsat</sub>	CEsat collector-emitter saturation voltage	$I_C$ = -10 mA; $I_B$ = -0.5 mA; $T_{amb}$ = 25 °C	-	-	-100	mV
		$I_C$ = -100 mA; $I_B$ = -5 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-	-400	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -10 mA; $I_B$ = -0.5 mA; $T_{amb}$ = 25 °C	-	-755	-	mV
V <sub>BE</sub>	base-emitter voltage	V <sub>CE</sub> = -5 V; I <sub>C</sub> = 2 mA; T <sub>amb</sub> = 25 °C	-600	-655	-750	mV
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	2.2	pF
C <sub>e</sub>	emitter capacitance	V <sub>EB</sub> = -0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	10	-	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
NF	noise figure	$V_{CE}$ = -5 V; $I_{C}$ = -0.2 mA; $R_{S}$ = 2 k $\Omega$ ; $f$ = 1 kHz; $B$ = 200 Hz; $T_{amb}$ = 25 °C	-	2	-	dB

#### PNP general purpose double transistor



V<sub>CE</sub> = -5 V (1) T<sub>amb</sub> = 150 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -55 °C

Fig. 3. PNP transistor: DC current gain as a function of Fig. 4. collector current; typical values

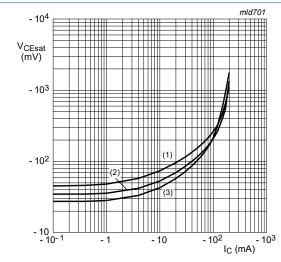


 $V_{CE} = -5 V$ (1)  $T_{amb} = -55 °C$ 

(2) T<sub>amb</sub> = 25 °C

 $(3) T_{amb} = 150 °C$ 

PNP TR2: Base-emitter voltage as a function of collector current; typical values



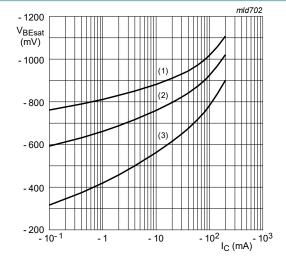
 $I_C/I_B = 20$ 

 $(1) T_{amb} = 150 °C$ 

(2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

**PNP TR2: Collector-emitter saturation voltage** Fig. 5. as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb}$  = 150 °C

Fig. 6. PNP TR2: Base-emitter saturation voltage as a function of collector current; typical values

#### PNP general purpose double transistor

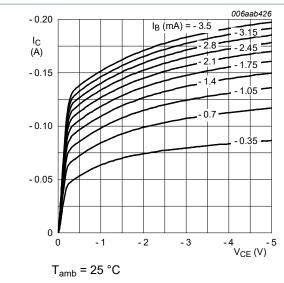


Fig. 7. PNP transistor: Collector current as a function of collector-emitter voltage; typical values

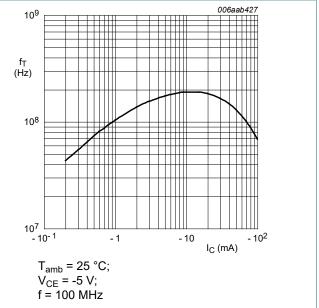


Fig. 8. PNP transistor: Transition frequency as a function of collector current; typical values

## 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## PNP general purpose double transistor

# 12. Package outline

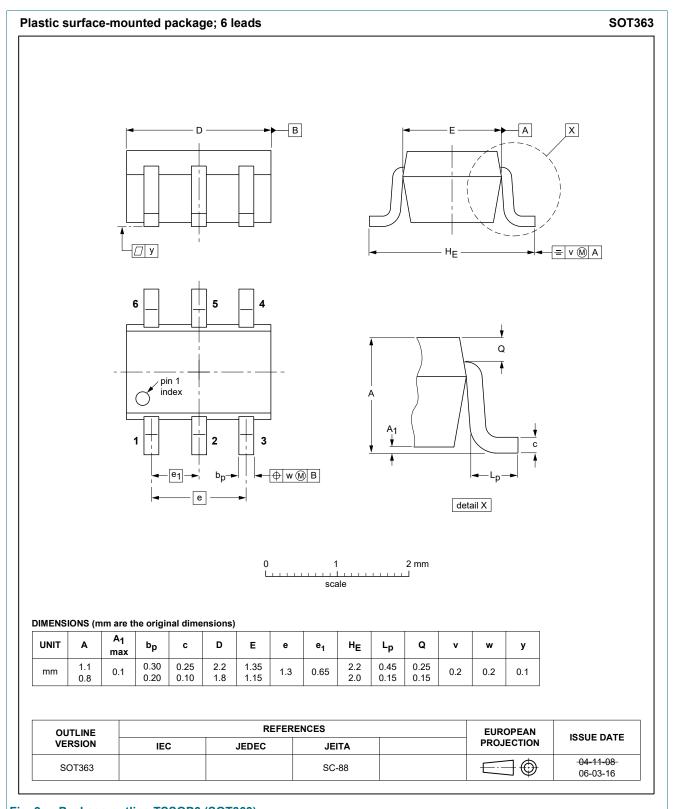
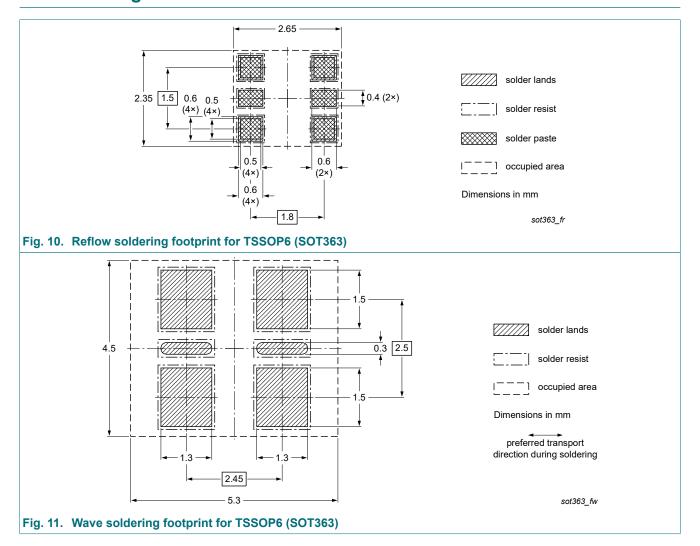


Fig. 9. Package outline TSSOP6 (SOT363)

## PNP general purpose double transistor

# 13. Soldering



## PNP general purpose double transistor

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC857BS-Q	20210629	Product data sheet	-	-

#### PNP general purpose double transistor

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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